

FEATURES

- PSRR: 100 dB minimum**
- CMRR: 105 dB typical**
- Very low supply current: 22 μ A maximum**
- 1.8 V to 5 V single-supply or ± 0.9 V to ± 2.5 V dual-supply operation**
- Rail-to-rail input and output**
- Low noise: 45 nV/ $\sqrt{\text{Hz}}$ @ 1 kHz**
- 2.5 mV offset voltage maximum**
- Very low input bias current: 1 pA typical**

APPLICATIONS

- Pressure and position sensors**
- Remote security**
- Bio sensors**
- IR thermometers**
- Battery-powered consumer equipment**
- Hazard detectors**

GENERAL DESCRIPTION

The AD8505 is a single micropower amplifiers featuring rail-to-rail input and output swings while operating from a single 1.8 V to 5 V power supply or from dual ± 0.9 V to ± 2.5 V power supplies.

Using a new circuit technology, these low cost amplifiers offer zero input crossover distortion (excellent PSRR and CMRR performance) and very low bias current, while operating with a supply current of less than 22 μ A per amplifier. This amplifier offers the lowest noise in its power class.

This combination of features makes the AD8505 amplifiers ideal choices for battery-powered applications because they minimize errors due to power supply voltage variations over the lifetime of the battery and maintain high CMRR even for a rail-to-rail input op amp.

PIN CONFIGURATIONS

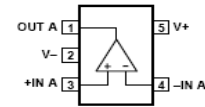
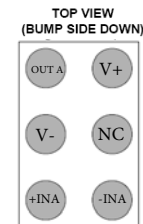


Figure 1. 5-Lead SOT23 (RJ-5)



NC = No Connect

Figure 2. 6-Ball WLCSP (CB-6-2)

Remote battery-powered sensors, handheld instrumentation and consumer equipment, hazard detection (for example, smoke, fire, and gas), and patient monitors can benefit from the features of the AD8505 amplifiers.

The AD8505 is specified for both the industrial temperature range of -40°C to $+85^{\circ}\text{C}$ and the extended industrial temperature range of -40°C to $+125^{\circ}\text{C}$. The AD8505 single amplifier is available in 5-lead SOT23 and 6-ball WLCSP packages.

The AD8505 is members of a growing series of zero crossover op amps offered by Analog Devices, Inc., including the AD8506/AD8508/ADA4505-1/ADA4505-2/ADA4505-4, which also operates from a single 1.8 V to 5 V supply or from dual ± 0.9 V to ± 2.5 V power supplies.

Rev. PrA

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SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—5 V OPERATION

$V_{SY} = 5\text{ V}$, $V_{CM} = V_{SY}/2$, $T_A = 25^\circ\text{C}$, $R_L = 100\text{ k}\Omega$ to GND, unless otherwise noted.

Table 1.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$0\text{ V} \leq V_{CM} \leq 5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	2.5	mV
Input Bias Current	I_B	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		1	10	pA
					100	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	5	pA
					50	pA
					130	pA
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		5	V
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	90	105		dB
			90			dB
			85			dB
Large Signal Voltage Gain	A_{VO}	$0.05\text{ V} \leq V_{OUT} \leq 4.95\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	105	120		dB
			100			dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2		$\mu\text{V}/^\circ\text{C}$
Input Resistance	R_{IN}			220		G Ω
Input Capacitance Differential Mode	C_{INDM}			3		pF
Input Capacitance Common Mode	C_{INCM}			4.2		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 100\text{ k}\Omega$ to GND $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	4.98	4.99		V
			4.98			V
			4.9	4.95		V
			4.9			V
Output Voltage Low	V_{OL}	$R_L = 100\text{ k}\Omega$ to V_{SY} $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2	5	mV
					5	mV
				10	25	mV
					30	mV
Short-Circuit Limit	I_{SC}	$V_{OUT} = V_{SY}$ or GND		± 45		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 1.8\text{ V}$ to 5 V $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	100	110		dB
			100			dB
			95			dB
Supply Current per Amplifier	I_{SY}	$V_{OUT} = V_{SY}/2$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		15	22	μA
					TBD	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 100\text{ k}\Omega$, $C_L = 10\text{ pF}$, $G = 1$		13		$\text{mV}/\mu\text{s}$
Gain Bandwidth Product	GBP	$R_L = 1\text{ M}\Omega$, $C_L = 20\text{ pF}$, $G = 1$		95		kHz
Phase Margin	Φ_M	$R_L = 1\text{ M}\Omega$, $C_L = 20\text{ pF}$, $G = 1$		60		Degrees
NOISE PERFORMANCE						
Voltage Noise	e_n p-p	$f = 0.1\text{ Hz}$ to 10 Hz		2.8		μV p-p
Voltage Noise Density	e_n	$f = 1\text{ kHz}$		45		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1\text{ kHz}$		15		$\text{fA}/\sqrt{\text{Hz}}$

ELECTRICAL CHARACTERISTICS—1.8 V OPERATION

$V_{SY} = 1.8\text{ V}$, $V_{CM} = V_{SY}/2$, $T_A = 25^\circ\text{C}$, $R_L = 100\text{ k}\Omega$ to GND, unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	2.5	mV
Input Bias Current	I_B	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		1	10	pA
					100	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	5	pA
					50	pA
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		1.8	V
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$	85	100		dB
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	85			dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	80			dB
Large Signal Voltage Gain	A_{VO}	$0.05\text{ V} \leq V_{OUT} \leq 1.75\text{ V}$	95	115		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	95			dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2.5		$\mu\text{V}/^\circ\text{C}$
Input Resistance	R_{IN}			220		G Ω
Input Capacitance Differential Mode	C_{INDM}			3		pF
Input Capacitance Common Mode	C_{INCM}			4.2		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 100\text{ k}\Omega$ to GND	1.78	1.79		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.78			V
		$R_L = 10\text{ k}\Omega$ to GND	1.65	1.75		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.65			V
Output Voltage Low	V_{OL}	$R_L = 100\text{ k}\Omega$ to V_{SY}		2	5	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			5	mV
		$R_L = 10\text{ k}\Omega$ to V_{SY}		12	25	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			25	mV
Short-Circuit Limit	I_{SC}	$V_{OUT} = V_{SY}$ or GND		± 4.5		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 1.8\text{ V}$ to 5 V	100	110		dB
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	100			dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	95			dB
Supply Current per Amplifier	I_{SY}	$V_{OUT} = V_{SY}/2$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		16.5	24	μA
					TBD	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 100\text{ k}\Omega$, $C_L = 10\text{ pF}$, $G = 1$		13		mV/ μs
Gain Bandwidth Product	GBP	$R_L = 1\text{ M}\Omega$, $C_L = 20\text{ pF}$, $G = 1$		95		kHz
Phase Margin	Φ_M	$R_L = 1\text{ M}\Omega$, $C_L = 20\text{ pF}$, $G = 1$		60		Degrees
NOISE PERFORMANCE						
Voltage Noise	e_n p-p	$f = 0.1\text{ Hz}$ to 10 Hz		2.8		μV p-p
Voltage Noise Density	e_n	$f = 1\text{ kHz}$		45		nV/ $\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1\text{ kHz}$		15		fA/ $\sqrt{\text{Hz}}$

ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
Supply Voltage	5.5 V
Input Voltage	$\pm V_{SY} \pm 0.1$ V
Input Current ¹	± 10 mA
Differential Input Voltage ²	$\pm V_{SY}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	-65°C to +150°C
Operating Temperature Range	-40°C to +125°C
Junction Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

¹ Input pins have clamp diodes to the supply pins. Input current should be limited to 10 mA or less whenever the input signal exceeds the power supply rail by 0.5 V.

² Differential input voltage is limited to 5 V or the supply voltage, whichever is less.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages. This was measured using a standard 2-layer board, unless otherwise specified.

Table 4. Thermal Resistance

Package Type	θ_{JA}	θ_{JB} ¹	θ_{JC}	Unit
5-Lead SOT23 (RJ-5)	TBD	TBD	TBD	°C/W
6-Ball WLCSP (CB-6-2)				
2-Layer PCB (1SOP)	TBD	TBD	N/A	°C/W
4-Layer PCB (2SOP)	TBD	TBD	N/A	°C/W

¹ Junction-to-board thermal resistance.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.